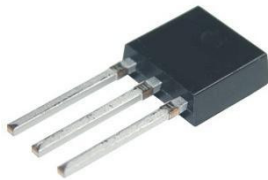
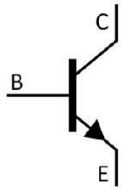


TO-251 NPN Silicon NPN transistor in a TO-251 Plastic Package.

2SA1930I

High f_T , complementary pair with 2SA1930I.

General power and driver stage amplifier applications.

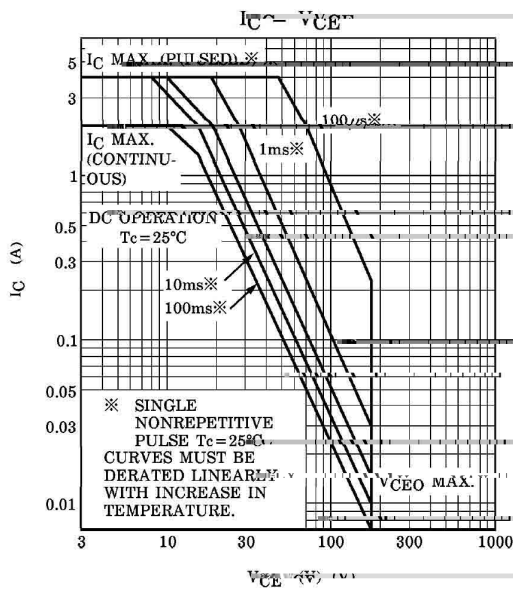
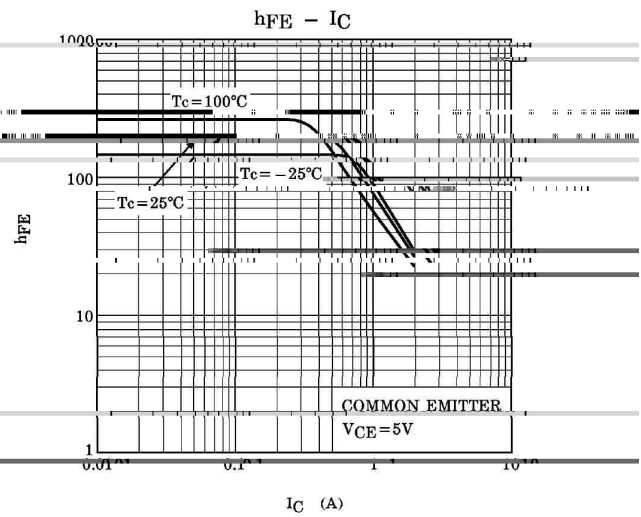
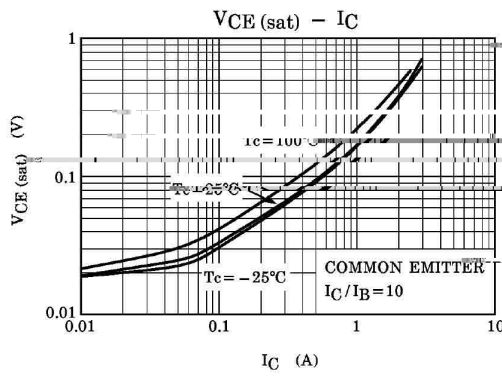
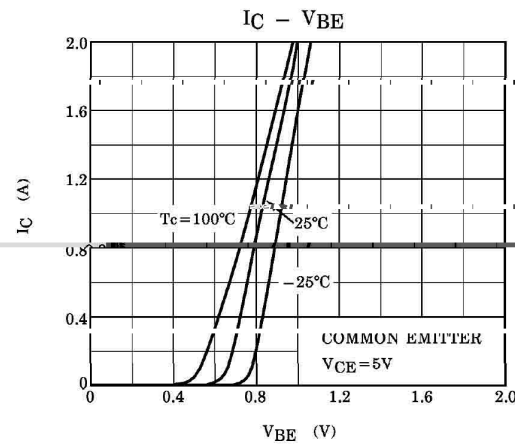
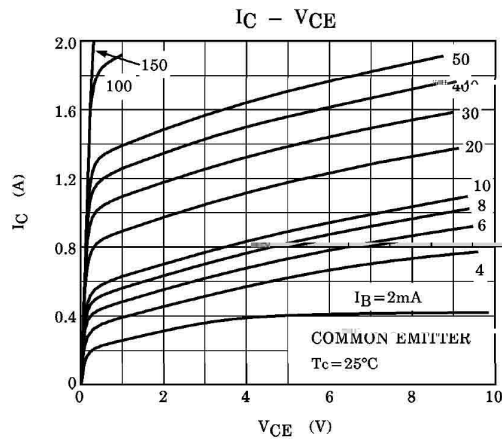


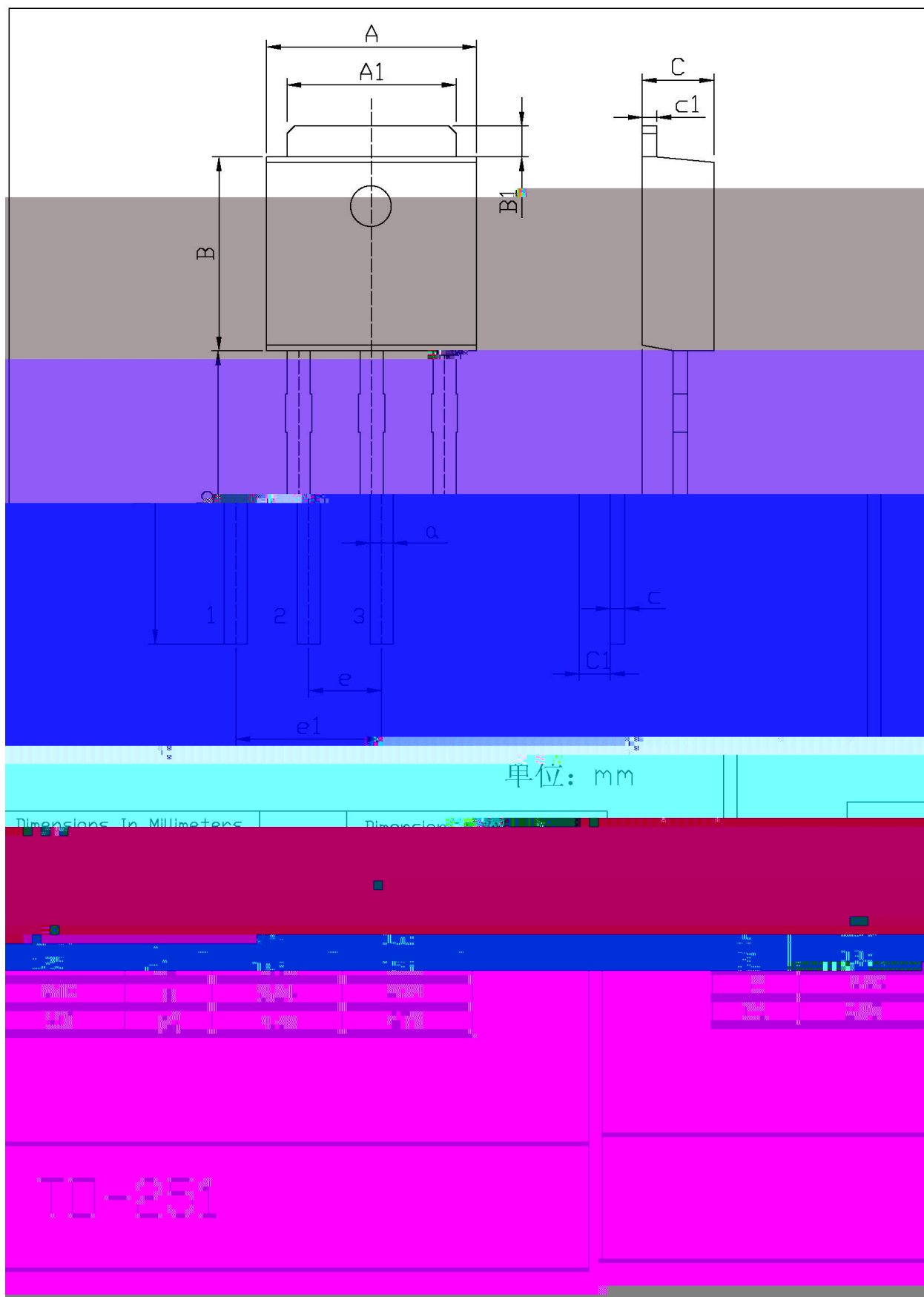
PIN1 Base PIN 2 Collector PIN 3 Emitter

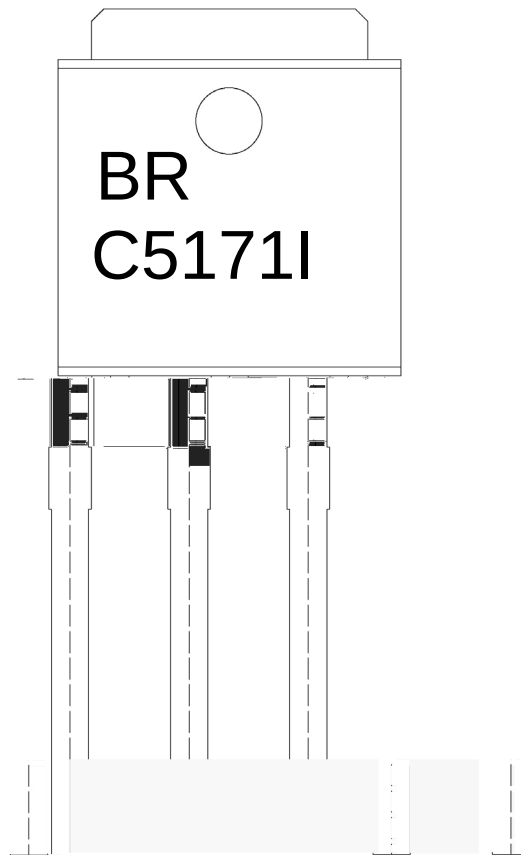
See Marking Instructions.

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	180	V
Collector to Emitter Voltage	V_{CEO}	180	V
Emitter to Base Voltage	V_{EBO}	5.0	V
Collector Current - Continuous	I_C	2.0	A
Base Current – Continuous	I_B	1.0	A
Collector Power Dissipation	P_C	1.5	W
Collector Power Dissipation	$P_C(T_c=25^\circ\text{C})$	20	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55~150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CBO}	$I_C=10\text{mA}$ $I_B=0$	180			V
Collector Cut-Off Current	I_{CBO}	$V_{CB}=180\text{V}$ $I_E=0$			5.0	μA
Emitter Cut-Off Current	I_{EBO}	$V_{EB}=5.0\text{V}$ $I_C=0$			5.0	μA
DC Current Gain	$h_{FE(1)}$	$V_{CE}=5.0\text{V}$ $I_C=100\text{mA}$	100		320	
	$h_{FE(2)}$	$V_{CE}=5.0\text{V}$ $I_C=1.0\text{A}$	50			
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=1.0\text{A}$ $I_B=100\text{mA}$		0.16	1.0	V
Base to Emitter Voltage	V_{BE}	$V_{CE}=5.0\text{V}$ $I_C=1.0\text{A}$		0.68	1.5	V
Transition Frequency	f_T	$V_{CE}=5.0\text{V}$ $I_C=300\text{mA}$		200		MHz
Collector output capacitance	C_{ob}	$V_{CB}=10\text{V}$ $I_E=0$ $f=1.0\text{MHz}$		16		pF







BR

C5171I

Note:

BR: Company Code

C5171I: Product Type.

****: Lot No. Code, code change with Lot No.



- 1

25

150

60

90sec;

2

255±5

5±0.5sec;

3

2

10

/sec.
- Note:

1.Preheating:25~150 , Time:60~90sec.

2.Peak Temp.:255±5 , Duration:5±0.5sec.

3. Cooling Speed: 2~10 /sec.

270±5

10±1 sec.

Temp.:270±5

Time:10±1 sec

/ BULK

Package Type	Units					Dimension		(unit mm ³)

/ TUBE

Package Type	Units					Dimension		(unit mm ³)